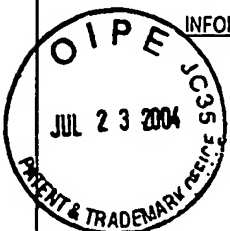


FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT 	MMB DOCKET NO. 1890-0038	APPLICATION NO.: 10/757,360
	APPLICANT(S): Kriz et al.	
	FILING DATE: January 13, 2004	GROUP ART UNIT: 2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
<i>CAL</i>	AA	6,319,786 B1	November 20, 2001	Gris	<div style="font-size: 4em;">X</div>		
	AB	5,185,276	February 9, 1993	Chen et al.			
	AC	5,204,276	April 20, 1993	Nakajima et al.			
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	AE	5,001,533	March 19, 1991	Yamaguchi			
	AF	2001/0005035 A1	June 28, 2001	Kinoshita			
<i>CAL</i>	AG	2001/0003667 A1	June 14, 2001.	Ahn et al.			
	AH						
	AI						
	AJ						
	AK						

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
<i>CAL</i>	AL	DE 3940674 A1	June 28, 1990	Germany	<div style="font-size: 4em;">X</div>		Yes No
<i>CAL</i>	AM	DE 3304642 A1	August 16, 1984	Germany			Yes No
<i>CAL</i>	AN	FR 2795233 A1	June 18, 1999	France			Yes No
<i>CAL</i>	AO	CA 01 201 218	February 25, 1986	Canada			Yes No
	AP						Yes No

## OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

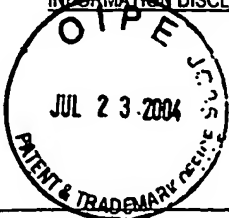
<i>CAL</i>	AQ	1	Pontcharra, de Jean, et al., "A 30-GHz $f_T$ Quasi-Self-Aligned Single-Poly Bipolar Technology", IEEE Transactions on Electron Devices, New York US, November 1, 1997, Volume 44, No. 11, pages 2091 – 2906, (6 pages).
<i>CAL</i>	AR	1	Sugiyama, M. et al., "A 40 GH $f_T$ Si Bipolar Transistor LSI Technology", Proceedings of the International Electron Devices Meeting, Washington, Dec. 3-6, 1989, New York US, December 3, 1989, Pages 221 – 224, (4 pages)
<i>CAL</i>	AS	1	Aoyama T. et al., "Selective Polysilicon Deposition (SPD) by Hot-Wall LPCVD and its Application to High Speed Bipolar Devices", Japanese Journal of Applied Physics, Tokyo, Japan 1990, pages 665 – 668, (4 pages).

EXAMINER

DATE CONSIDERED

8/3/05

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT 	MMB DOCKET NO. 1890-0038	APPLICATION NO.: 10/757,360
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	BA						
	BB						
	BC						
	BD						
	BE						
	BF						
	BG						
	BH						
	BI						
	BJ						
	BK						

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	BL						Yes No
	BM						Yes No
	BN						Yes No
	BO						Yes No
	BP						Yes No

## OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>cal</i>	AQ	2	Burghartz J. N. et al., "Novel In-Situ Doped Polysilicon Emitter Process with Buried Diffusion Source (BDS)", IEEE Electron Device Letters, Volume 12, No. 12, New York US, December 1991, pages 679 – 681, (3 pages).
<i>cal</i>	AR	2	Selvakumar, C. R., "Theoretical and Experimental Aspects of Polysilicon Emitter Bipolar Transistors", IEEE, November 16, 1988, pages 3 – 16, (14 pages).
	AS	2	

EXAMINER

*cfu*

DATE CONSIDERED

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